

Production and Quality Control Datasheet Schottky Receiver



1.0 General

Order Number	VB.21.02659
Institute/Company	Oklahoma State University
Production Date	08.02.2022

2.0 Components

Schottky Diode	Receiver SCHOTTKY-FD-RX-1 Zero-bias Schottky diode, high-responsivity model	SN 43-41
Package	Lens: Si lens, \varnothing 12 mm Electrical connector: SMA Output impedance: 50 Ω	
Typical NEP	7 pW/sqrt(Hz) @ 100 GHz 100 pW/sqrt(Hz) @ 1 THz	
Typical Responsivity	22000 V/W @ 100 GHz 1100 V/W @ 1 THz	
Amplifier	Integrated transimpedance amplifier, Gain factor: 10^5 V/A Bandwidth 10 Hz – 1 MHz	

CAUTION!	Schottky diodes are electrostatic-discharge sensitive devices! We recommend to always wear a high-impedance grounding strap for handling.
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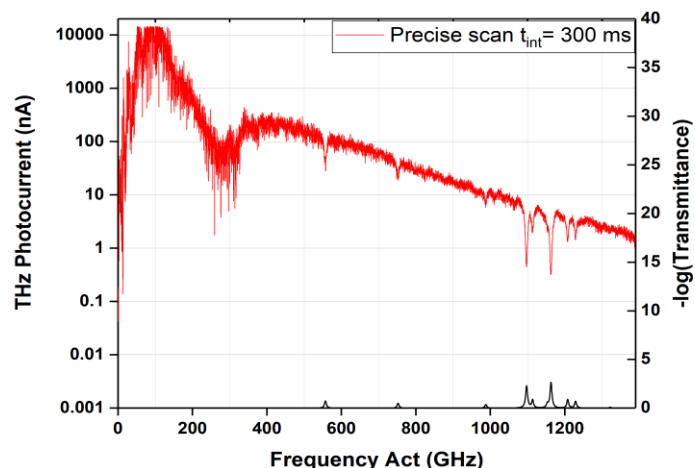
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3.0 Measurements

Laser Heads	DFB pro BFY THz L heads, SN 33369 + 33362		
	Wavelengths: 1550 nm + 1545 nm		
	Optical power before mating sleeve: 33 mW		
Electronics	DLC smart, SN 015163		
Lock-in Detection Settings	Emitter Bias: -0.4 V DC \pm 0.9 V AC (Offset \pm Modulation Amplitude)		
	Modulation Frequency: 39.7 kHz		
	Lock-in Phase: 95.3 deg		
	Integration Time: 3 ms / 300 ms		
Terahertz Emitter	PCA-FD-1550-100-TX-1, InGaAs photodiode photomixer, SN TC211009		
Receiver Characteristics	Noise:		
	<ul style="list-style-type: none">40 pA @ 3 ms lock-in integration time4.3 pA @ 300 ms lock-in integration time		
Terahertz Characteristics	Frequency	100 GHz	500 GHz
	Receiver photocurrent	2880 nA	121 nA
		12 nA	
Terahertz Spectrum			



4.0 Instructions and Comments

5.0 Quality Control

Production	Cansu Arpacioglu	Date	08.02.2022
Final Check		Date	08.02.2022